

Date Mailed: April 19, 2006

Sheet 1 of 6

Form 1449*

**INFORMATION DISCLOSURE STATEMENT
IN AN APPLICATION FOR A PATENT**

Docket Number: G&C 30794.93-US-WO

Application Number: 10/537,644

Applicant: Benjamin A. Haskell et al.

Filing Date: June 6, 2005

Group Art Unit: 2823

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WC	6,900,070	05/31/2005	Craven et al.			
WC	6,645,295	11/11/2003	Koike et al.			
WC	6,635,901	10/21/2003	Sawaki et al.			
WC	6,623,560	09/2003	Biwa et al.			
WC	6,602,763	08/05/2003	Davis et al.			
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WC	6,413,627	07/02/2002	Motoki et al.			
WC	6,350,666	02/26/2002	Kryliouk			
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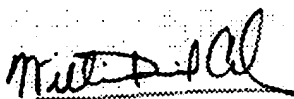
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						YES	NO
WC	WO 2004/061969	07/22/2004	PCT				
WC	WO 2005/064643	07/14/2005	PCT				
WC	WO 2004/061909	07/22/2004	PCT				
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WC	2001 257166	09/21/2001	Japan (Abstract only)				
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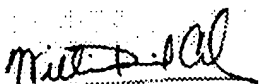
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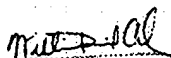
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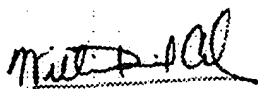
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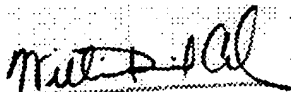


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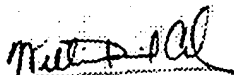
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Form 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION	Docket Number: G&C 30794.93-US-WO	Application Number 10/537,644
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